

Silicon Carbide (SiC) MOSFET – EliteSiC, 40 mohm, 1200 V, M3S, TO-247-4L

NVH4L040N120M3S

Features

- Typ. $R_{DS(on)}$ = 40 mΩ @ V_{GS} = 18 V
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 75 nC)
- High Speed Switching with Low Capacitance (C_{oss} = 80 pF)
- 100% Avalanche Tested
- AEC-Q101 Qualified and PPAP Capable
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Typical Applications

- Automotive On Board Charger
- Automotive DC-DC Converter for EV/HEV

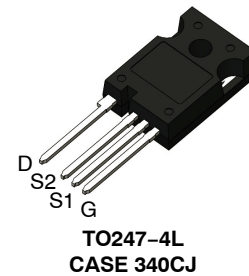
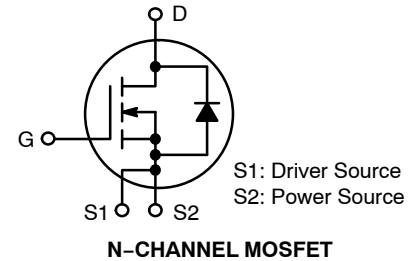
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Parameter | | Symbol | Value | Unit | |
|--|-----------------------|--|-----------------|------|---|
| Drain-to-Source Voltage | | V _{DSS} | 1200 | V | |
| Gate-to-Source Voltage | | V _{GS} | -10/+22 | V | |
| Recommended Operation Values of Gate-to-Source Voltage | | T _C <175°C V _{GSop} | -3/+18 | V | |
| Continuous Drain Current (Notes 1, 3) | Steady State | T _C =25°C | I _D | 54 | A |
| Power Dissipation (Note 1) | | | P _D | 231 | W |
| Continuous Drain Current (Notes 1, 3) | Steady State | T _C =100°C | I _D | 38 | A |
| Power Dissipation (Note 1) | | | P _D | 115 | W |
| Pulsed Drain Current (Note 2) | T _C = 25°C | | I _{DM} | 134 | A |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C | |
| Source Current (Body Diode) T _C = 25°C, V _{GS} = -3 V | | I _S | 45 | A | |
| Single Pulse Drain-to-Source Avalanche Energy (Note 4) | | E _{AS} | 143 | mJ | |
| Maximum Lead Temperature for Soldering (1/25" from case for 10 s) | | T _L | 270 | °C | |

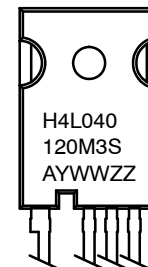
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. The maximum current rating is based on typical $R_{DS(on)}$ performance.
4. EAS of 143 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1\text{ mH}$, $I_{AS} = 16.9\text{ A}$, $V_{DD} = 100\text{ V}$, $V_{GS} = 18\text{ V}$.

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 1200 V | 54 mΩ @ 18 V | 54 A |



MARKING DIAGRAM



H4L040120M3S = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------------|----------|-----------------|
| NVH4L040N120M3S | TO247-4L | 30 Units / Tube |

NVH4L040N120M3S

Table 1. THERMAL CHARACTERISTICS

| Parameter | Symbol | Max | Unit |
|---|-----------------|------|------|
| Junction-to-Case – Steady State (Note 1) | $R_{\theta JC}$ | 0.65 | °C/W |
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 40 | |

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

OFF-STATE CHARACTERISTICS

| | | | | | | |
|---|-------------------|--|------|-----|-----|------|
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$ | 1200 | – | – | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = 1\text{ mA}$, referenced to 25°C (Note 6) | – | 0.3 | – | V/°C |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ | – | – | 100 | μA |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{GS} = +22/-10\text{ V}, V_{DS} = 0\text{ V}$ | – | – | ±1 | μA |

ON-STATE CHARACTERISTICS (Note 2)

| | | | | | | |
|-------------------------------|--------------|---|------|-----|-----|----|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 10\text{ mA}$ | 2.04 | 2.9 | 4.4 | V |
| Recommended Gate Voltage | V_{GOP} | | –3 | – | +18 | V |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 18\text{ V}, I_D = 20\text{ A}, T_J = 25^\circ\text{C}$ | – | 40 | 54 | mΩ |
| | | $V_{GS} = 18\text{ V}, I_D = 20\text{ A}, T_J = 175^\circ\text{C}$ (Note 6) | – | 80 | – | |
| Forward Transconductance | g_{FS} | $V_{DS} = 10\text{ V}, I_D = 20\text{ A}$ (Note 6) | – | 16 | – | S |

CHARGES, CAPACITANCES & GATE RESISTANCE

| | | | | | | |
|------------------------------|--------------|--|---|------|---|----|
| Input Capacitance | C_{ISS} | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 800\text{ V}$ (Note 6) | – | 1700 | – | pF |
| Output Capacitance | C_{OSS} | | – | 80 | – | |
| Reverse Transfer Capacitance | C_{RSS} | | – | 7 | – | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = -3/18\text{ V}, V_{DS} = 800\text{ V}, I_D = 20\text{ A}$ (Note 6) | – | 75 | – | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | – | 4.4 | – | |
| Gate-to-Source Charge | Q_{GS} | | – | 14 | – | |
| Gate-to-Drain Charge | Q_{GD} | | – | 22 | – | |
| Gate-Resistance | R_G | $f = 1\text{ MHz}$ | – | 3.8 | – | Ω |

SWITCHING CHARACTERISTICS

| | | | | | | |
|-------------------------|--------------|---|---|-----|---|----|
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = -3/18\text{ V}, V_{DS} = 800\text{ V}, I_D = 20\text{ A}, R_G = 4.7\text{ }\Omega$ Inductive load (Notes 5, 6) | – | 12 | – | ns |
| Rise Time | t_r | | – | 15 | – | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | – | 35 | – | |
| Fall Time | t_f | | – | 10 | – | |
| Turn-On Switching Loss | E_{ON} | | – | 182 | – | μJ |
| Turn-Off Switching Loss | E_{OFF} | | – | 66 | – | |
| Total Switching Loss | E_{tot} | | – | 248 | – | |

SOURCE-DRAIN DIODE CHARACTERISTICS

| | | | | | | |
|--|-----------|--|---|-----|-----|---|
| Continuous Source-Drain Diode Forward Current | I_{SD} | $V_{GS} = -3\text{ V}, T_C = 25^\circ\text{C}$ (Note 6) | – | – | 45 | A |
| Pulsed Source-Drain Diode Forward Current (Note 2) | I_{SDM} | | – | – | 134 | |
| Forward Diode Voltage | V_{SD} | $V_{GS} = -3\text{ V}, I_{SD} = 20\text{ A}, T_J = 25^\circ\text{C}$ | – | 4.5 | – | V |

NVH4L040N120M3S

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|-----------|---|-----|------|-----|---------------|
| SOURCE-DRAIN DIODE CHARACTERISTICS | | | | | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = -3/18\text{ V}$, $I_{SD} = 20\text{ A}$, $dI_S/dt = 1000\text{ A}/\mu\text{s}$, $V_{DS} = 800\text{ V}$ (Note 6) | – | 16.8 | – | ns |
| Reverse Recovery Charge | Q_{RR} | | – | 82 | – | nC |
| Reverse Recovery Energy | E_{REC} | | – | 7.9 | – | μJ |
| Peak Reverse Recovery Current | I_{RRM} | | – | 9.8 | – | A |
| Charge Time | T_A | | – | 9.6 | – | ns |
| Discharge Time | T_B | | – | 7.2 | – | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. E_{ON}/E_{OFF} result is with body diode.

6. Defined by design, not subject to production test.

TYPICAL CHARACTERISTICS

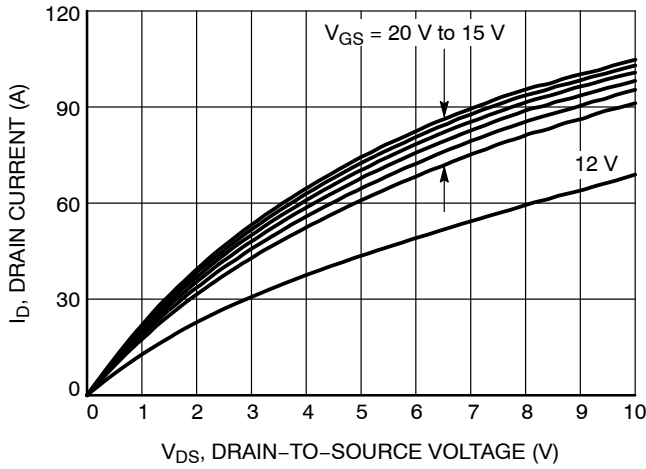


Figure 1. On-Region Characteristics

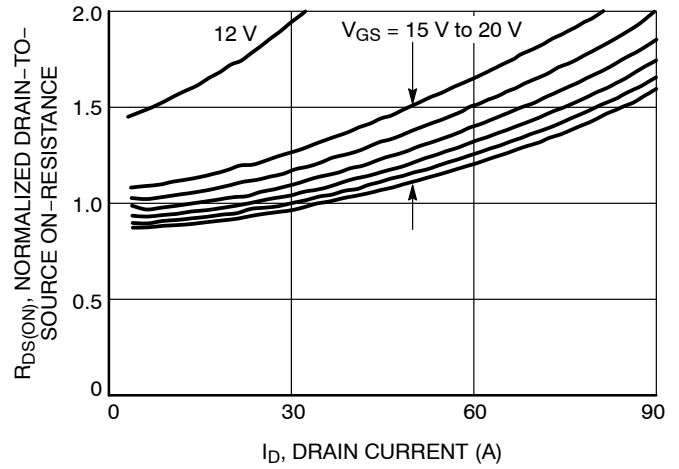


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

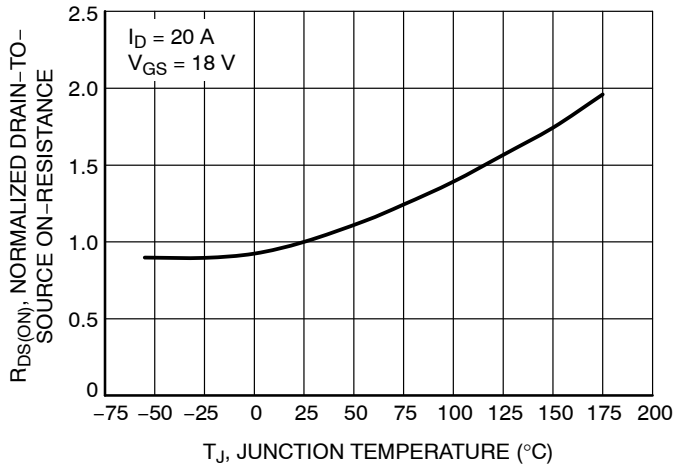


Figure 3. On-Resistance Variation with Temperature

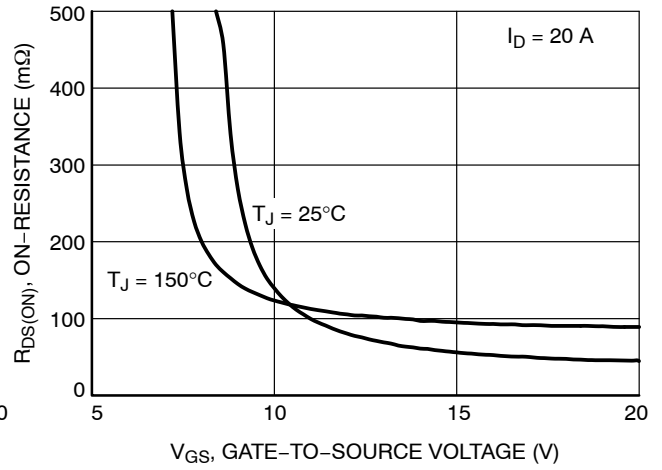


Figure 4. On-Resistance vs. Gate-to-Source Voltage

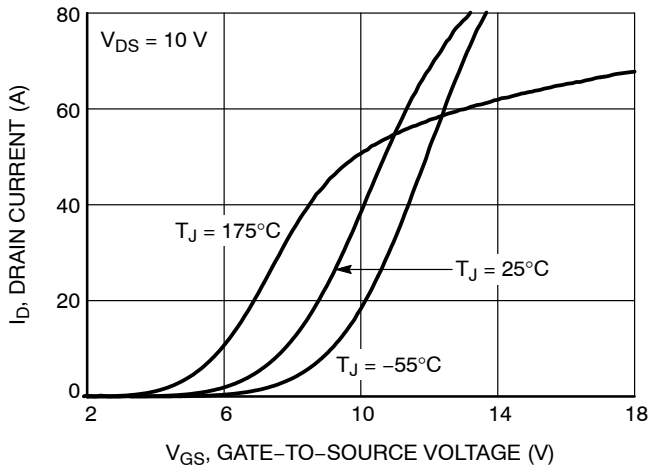


Figure 5. Transfer Characteristics

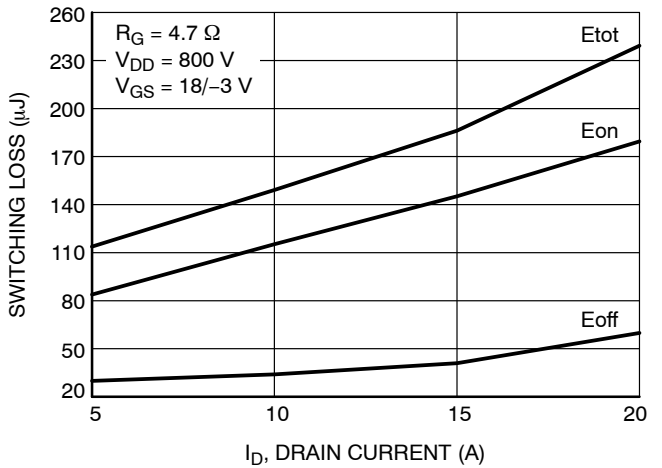


Figure 6. Switching Loss vs. Drain Current

TYPICAL CHARACTERISTICS

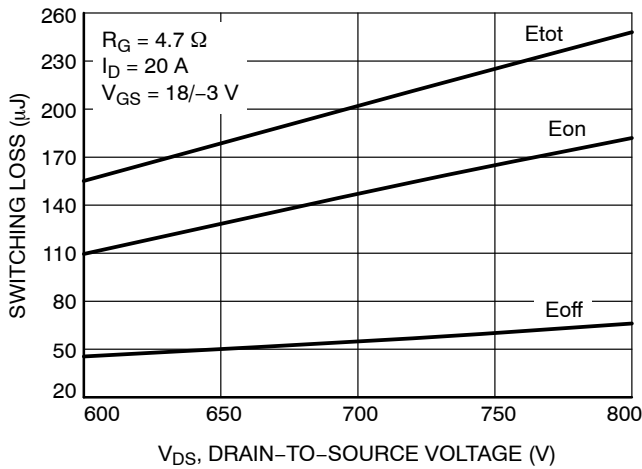


Figure 7. Switching Loss vs. Drain-to-Source Voltage

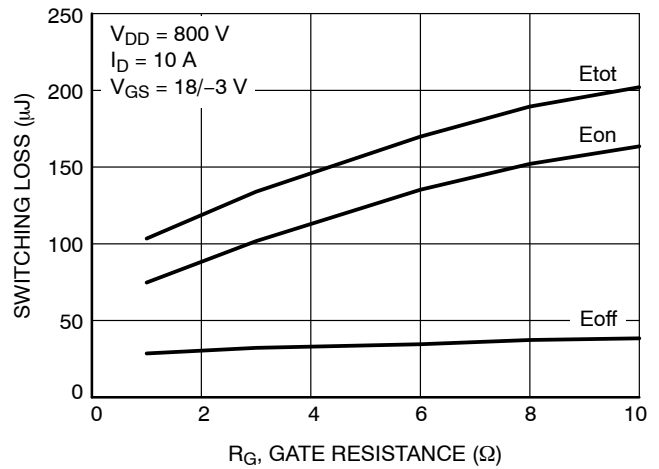


Figure 8. Switching Loss vs. Gate Resistance

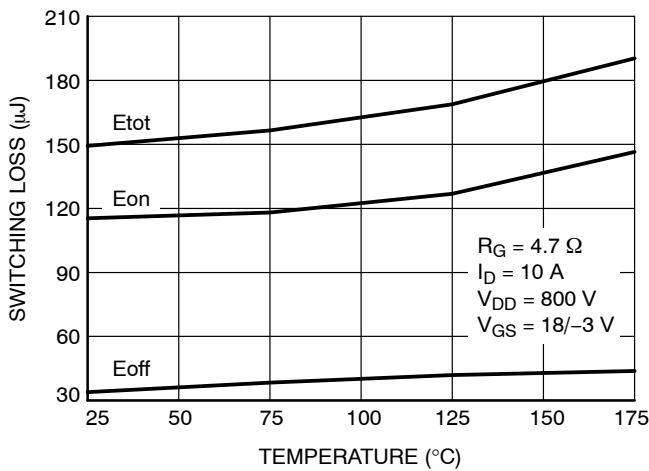


Figure 9. Switching Loss vs. Temperature

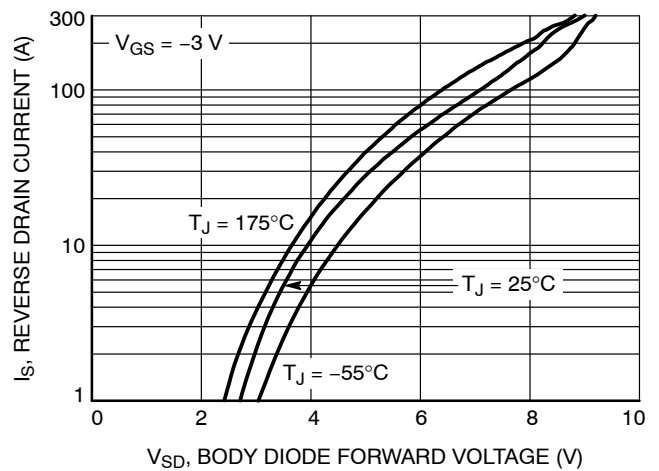


Figure 10. Reverse Drain Current vs. Body Diode Forward Voltage

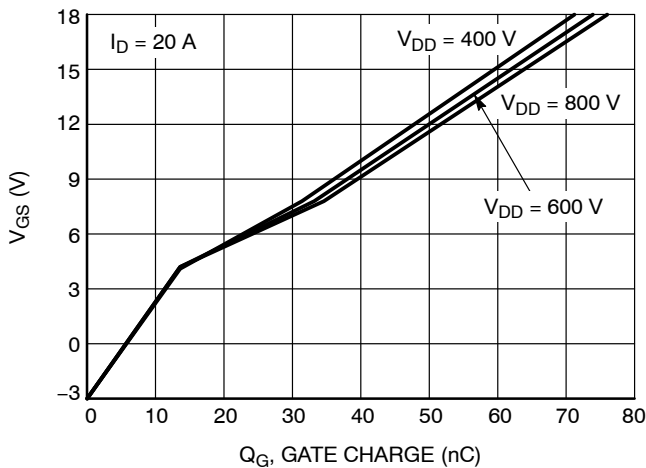


Figure 11. Gate-to-Source Voltage vs. Total Charge

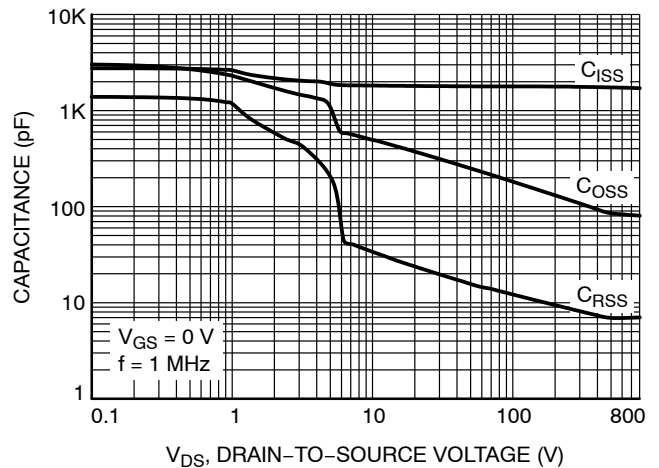


Figure 12. Capacitance vs. Drain-to-Source Voltage

TYPICAL CHARACTERISTICS

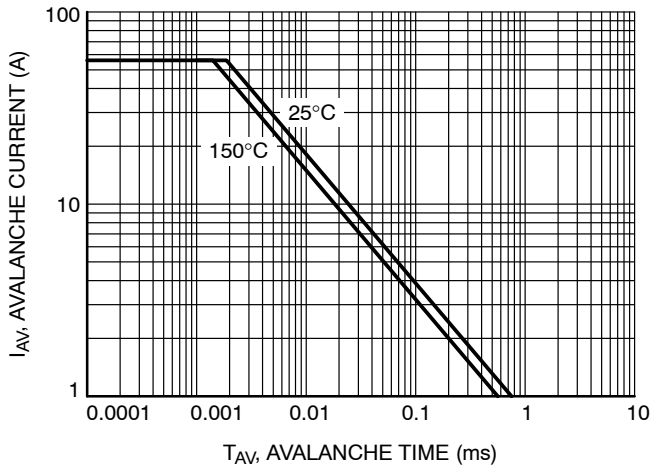


Figure 13. Unclamped Inductive Switching Capability

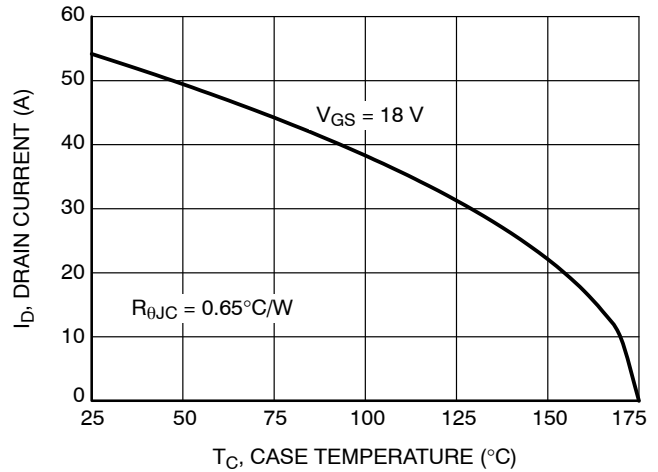


Figure 14. Maximum Continuous Drain Current vs. Case Temperature

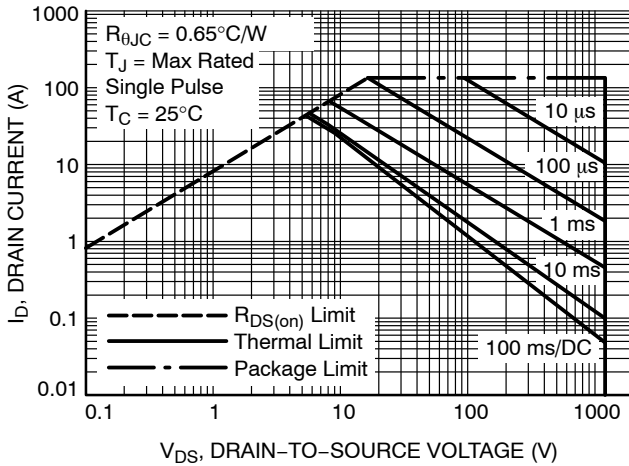


Figure 15. Safe Operating Area

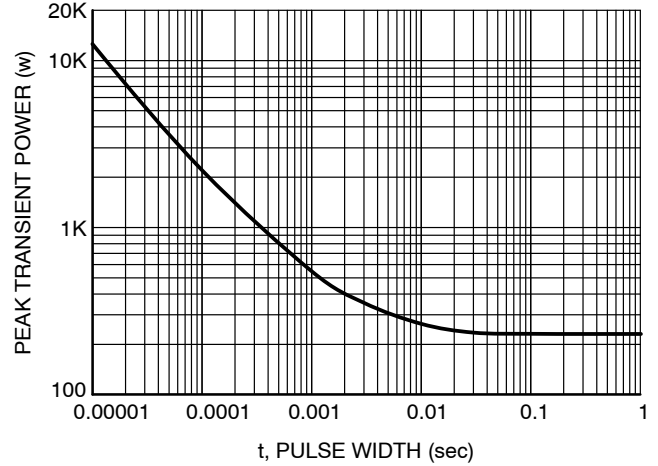


Figure 16. Single Pulse Maximum Power Dissipation

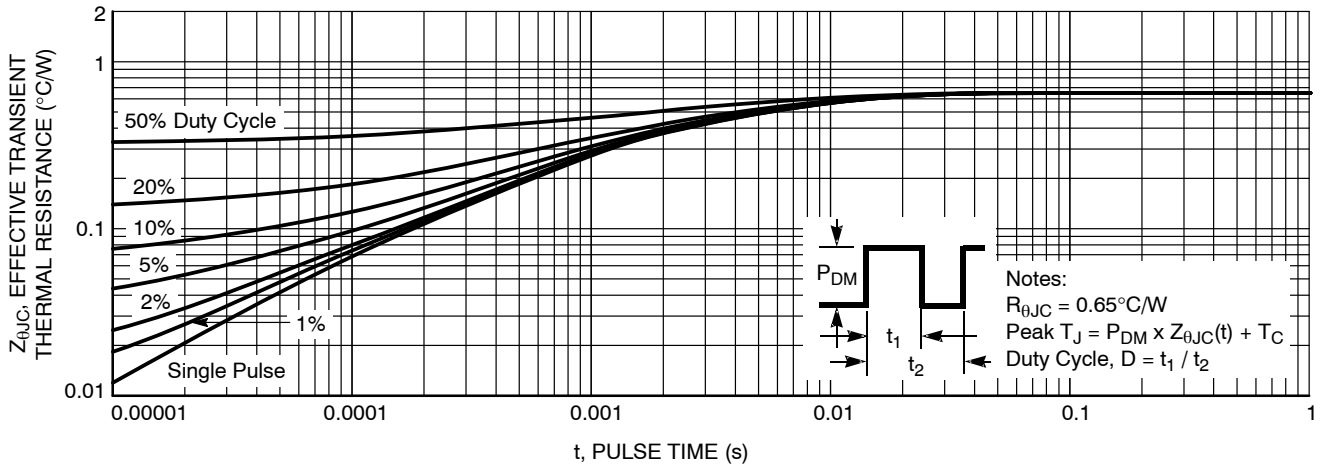


Figure 17. Junction-to-Case Transient Thermal Response

MECHANICAL CASE OUTLINE

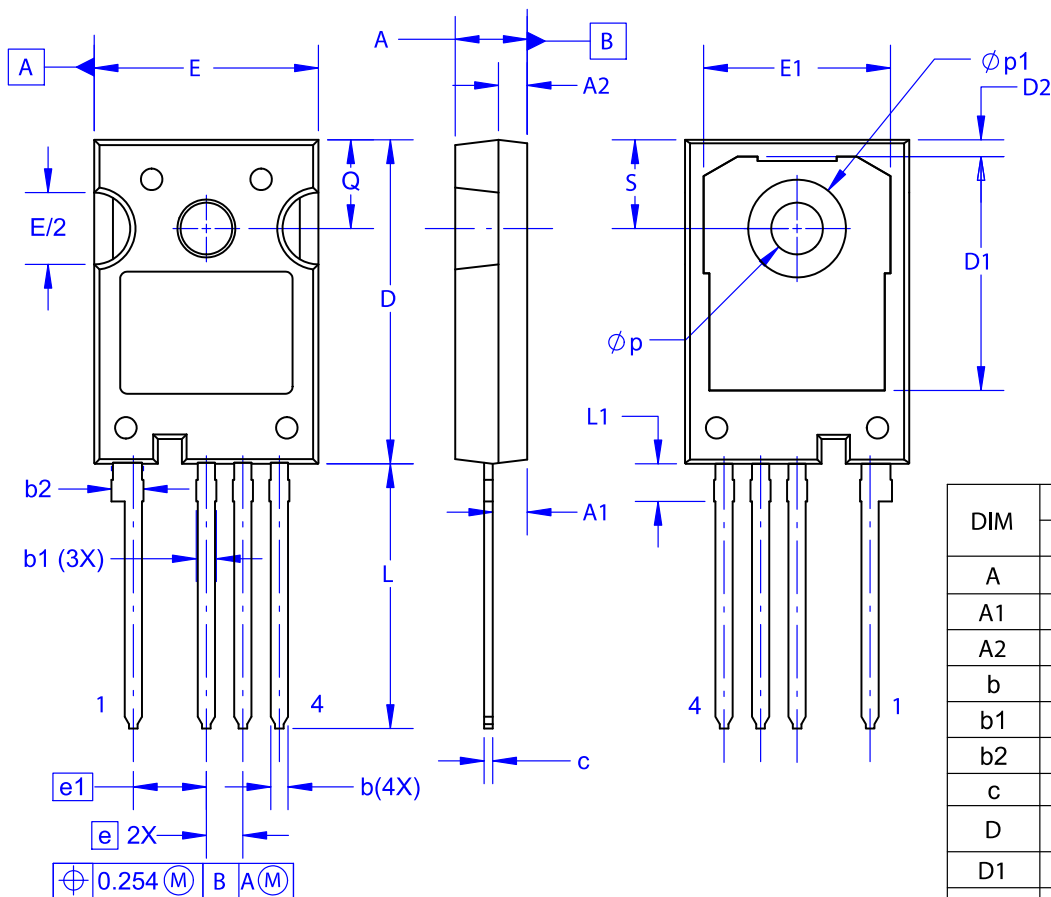
PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019



| DIM | MILLIMETERS | | |
|-----|-------------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.80 | 5.00 | 5.20 |
| A1 | 2.10 | 2.40 | 2.70 |
| A2 | 1.80 | 2.00 | 2.20 |
| b | 1.07 | 1.20 | 1.33 |
| b1 | 1.20 | 1.40 | 1.60 |
| b2 | 2.02 | 2.22 | 2.42 |
| c | 0.50 | 0.60 | 0.70 |
| D | 22.34 | 22.54 | 22.74 |
| D1 | 16.00 | 16.25 | 16.50 |
| D2 | 0.97 | 1.17 | 1.37 |
| e | 2.54 BSC | | |
| e1 | 5.08 BSC | | |
| E | 15.40 | 15.60 | 15.80 |
| E1 | 12.80 | 13.00 | 13.20 |
| E/2 | 4.80 | 5.00 | 5.20 |
| L | 18.22 | 18.42 | 18.62 |
| L1 | 2.42 | 2.62 | 2.82 |
| p | 3.40 | 3.60 | 3.80 |
| p1 | 6.60 | 6.80 | 7.00 |
| Q | 5.97 | 6.17 | 6.37 |
| S | 5.97 | 6.17 | 6.37 |

NOTES:

- NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
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- ALL DIMENSIONS ARE IN MILLIMETERS.
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